



#### **DUAL COMPLEMENTARY PRE-BIASED TRANSISTORS**

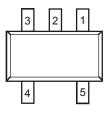
#### **Features**

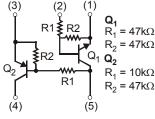
- Ultra-Small Surface Mount Package
- Epitaxial Planar Die Construction
- Surface Mount Package Suited for Automated Assembly
- · Simplifies Circuit Design and Reduces Board Space
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

### **Mechanical Data**

- Case: SOT353
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208 <a>@3</a>
- Weight: 0.006 grams (approximate)







Package Pin Out Configuration

Device Schematic

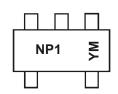
### Ordering Information (Notes 4 & 5)

Ī	Part Number	Compliance	Marking	Reel size (inch)	Tape width (mm)	Quantity per reel
	UMC4N-7	AEC-Q101	NP1	7	8	3,000
	UMC4NQ-7	Automotive	NP1	7	8	3.000

Notes:

- $1.\ No\ purposely\ added\ lead.\ Fully\ EU\ Directive\ 2002/95/EC\ (RoHS)\ \&\ 2011/65/EU\ (RoHS\ 2)\ compliant.$
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com.

# Marking Information



NP1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	2010		2011	2012		2013	2014		2015	2016		2017
Code	Х		Υ	Z		Α	В		С	D		Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



#### Maximum Ratings, Pre-Biased NPN Transistor, Q<sub>1</sub> (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage	V <sub>CC</sub>	50	V
Input Voltage	V <sub>IN</sub>	-10 to +40	V
Output Current	I <sub>0</sub>	30	mA
Collector Current	Ic	100	mA

## Maximum Ratings, Pre-Biased PNP Transistor, Q<sub>2</sub> (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage	Vcc	-50	V
Input Voltage	$V_{IN}$	-40 to +6	V
Output Current	lo	-100	mA
Collector Current	Ic	-100	mA

## **Thermal Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	$P_{D}$	150	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{ hetaJA}$	833	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

## Electrical Characteristics, Pre-Biased NPN Transistor, Q<sub>1</sub> (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	(Note 7)	V <sub>I(OFF)</sub>	0.5	_	_	V	$V_{CC} = 5V$ , $I_{O} = 100 \mu A$
input voltage	(Note 8)	$V_{I(ON)}$	_		3	V	$V_0 = 0.3V, I_0 = 2mA$
Output Voltage		V <sub>O(ON)</sub>	_	0.1	0.3	V	$I_{O} / I_{I} = 10 \text{mA} / 0.5 \text{ mA}$
Input Current		l <sub>l</sub>	_	_	0.18	mA	V <sub>I</sub> = 5V
Output Current		I <sub>O(OFF)</sub>	_	_	0.5	μΑ	$V_{CC} = 50V, V_I = 0V$
DC Current Gain		Gı	68	_	_	_	$V_O = 5V$ , $I_O = 5mA$
Gain-Bandwidth Product (Note 9)		f <sub>T</sub>	_	250	_	MHz	$V_{CE} = 10V$ , $I_{E} = -5mA$ , $f = 100MHz$
Input Resistance		R <sub>1</sub>	32.9	47	61.1	kΩ	_
Resistance Ratio		R <sub>2</sub> /R <sub>1</sub>	0.8	1	1.2	_	_

Note:

- 7. The device is guaranteed to be in "OFF" state with  $V_{I(OFF)}$  up to 0.5V
- 8. The device is guaranteed to be in "ON" state with  $V_{I(ON)}$  starting from 3V
- 9. Characteristic of Transistor for reference only.

## Electrical Characteristics, Pre-Biased PNP Transistor, Q2 (@TA = +25°C unless otherwise specified.)

Chara	Symbol	Min	Тур	Max	Unit	Test Condition	
Input Voltage	(Note 10)	$V_{I(OFF)}$	-0.3	_	_	V	$V_{CC} = -5V, I_{O} = -100\mu A$
input voitage	(Note 11)	V <sub>I(ON)</sub>	_	_	-1.4	V	$V_O = -0.3V$ , $I_O = -1mA$
Output Voltage		V <sub>O(ON)</sub>	_	-0.1	-0.3	V	$I_0/I_1 = -5 \text{mA}/-0.25 \text{ mA}$
Input Current		l <sub>l</sub>	_	_	-0.88	mA	V <sub>I</sub> = -5V
Output Current		I <sub>O(OFF)</sub>	_	_	-0.5	μΑ	$V_{CC} = -50V, V_I = 0V$
DC Current Gain		Gı	68	_	_	_	$V_{O} = -5V, I_{O} = -5mA$
Gain-Bandwidth Product (Note 12)		f⊤	_	250	_	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f = 100MHz
Input Resistance		R <sub>1</sub>	7	10	13	kΩ	_
Resistance Ratio		R <sub>2</sub> /R <sub>1</sub>	3.7	4.7	5.7	_	_

Note:

- 10. The device is guaranteed to be in "OFF" state with  $V_{I(OFF)}$  up to -0.3V
- 11. The device is guaranteed to be in "ON" state with V<sub>I(ON)</sub> starting from -1.4V
- 12. Characteristic of Transistor for reference only.

<sup>6.</sup> For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.



## Typical Electrical Characteristics (@TA = +25°C unless otherwise specified.)

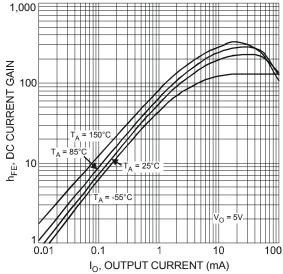
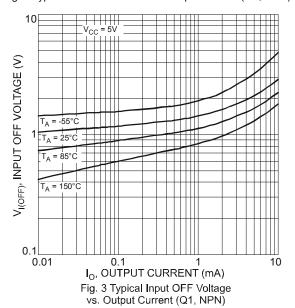


Fig. 1 Typical DC Current Gain vs. Output Current (Q1, NPN)



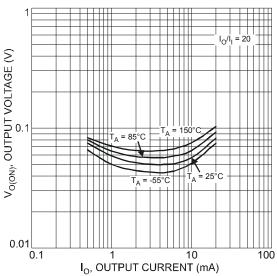
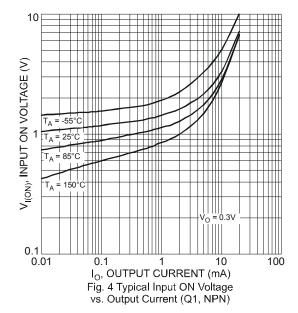
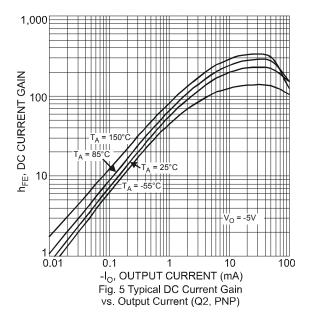
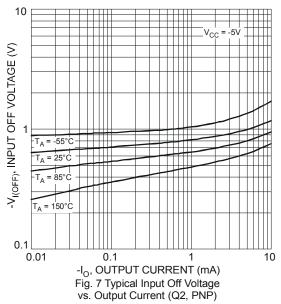


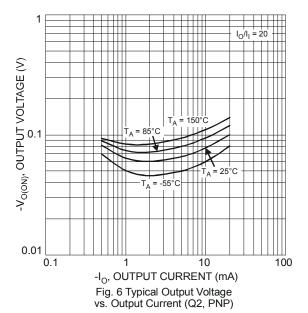
Fig. 2 Typical Output Voltage vs. Output Current (Q1, NPN)

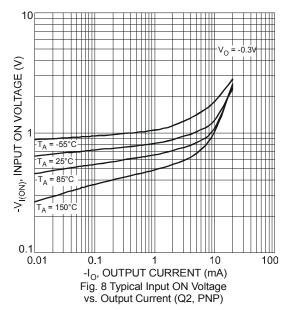








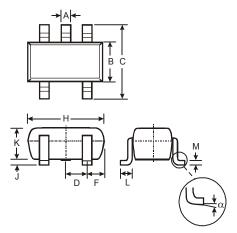






# **Package Outline Dimensions**

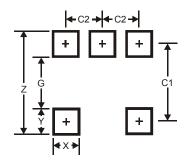
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT353							
Dim	Min	Max					
Α	0.10	0.30					
В	1.15	1.35					
C	2.00	2.20					
D	0.65 Typ						
F	0.40	0.45					
Н	1.80	2.20					
7	0	0.10					
K	0.90	1.00					
L	0.25	0.40					
М	0.10	0.22					
α	0°	8°					
All Di	mensions	in mm					

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65



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